

60V 3.5mohm N-channel SGT MOSFET AKG6N035GL

Description:

This N channel SGT MOSFET has been designed to very low on-state resistance and maintain superior switching performance, especial for high efficiency power management applications.

Features:

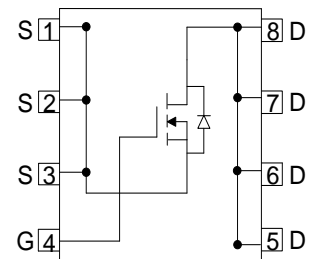
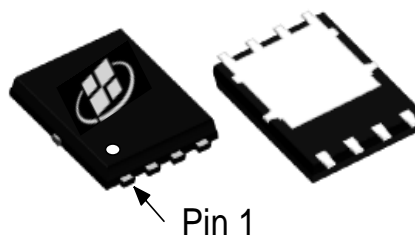
- Low $R_{DS(ON)}$
- RoHS compliant ^(Note 1)
- Halogen-free ^(Note 1)

Applications:

- Battery Management System
- Motor Drivers
- DC-DC Converter

Key Performance Parameters:

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(ON), max} @ V_{GS} = 10V$	3.5	m Ω
I_D	100	A



Ordering Information:

Ordering Code	Package Type	Marking Code	Form	Packing
AKG6N035GL	DFN5X6	G6N035GL	Tape Reel	5000PCS

Notes:

1. Contact ALKAIDSEMI sales for detail information

Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source Voltage	60	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) ^(Note 1)	100	A
	Drain Current - Continuous ($T_C = 100^\circ\text{C}$)	63	A
I_{DM}	Drain Current - Pulsed ^(Note 2)	400	A
V_{GS}	Gate-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy ^(Note 3)	196	mJ
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$)	62	W
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

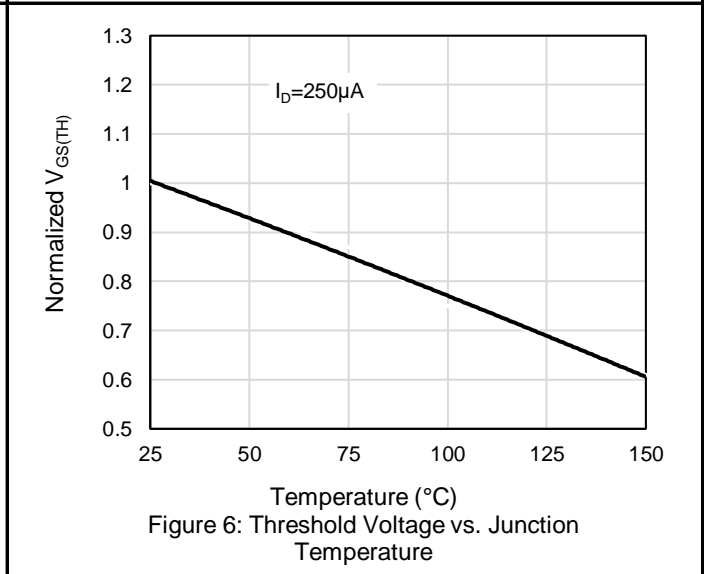
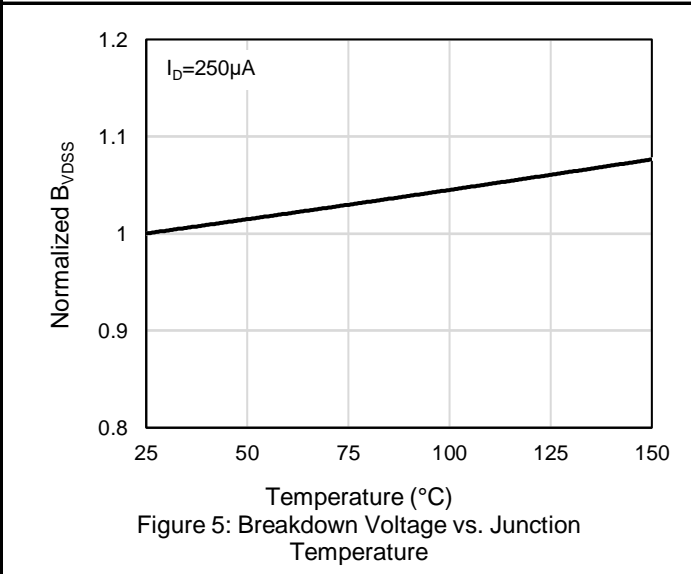
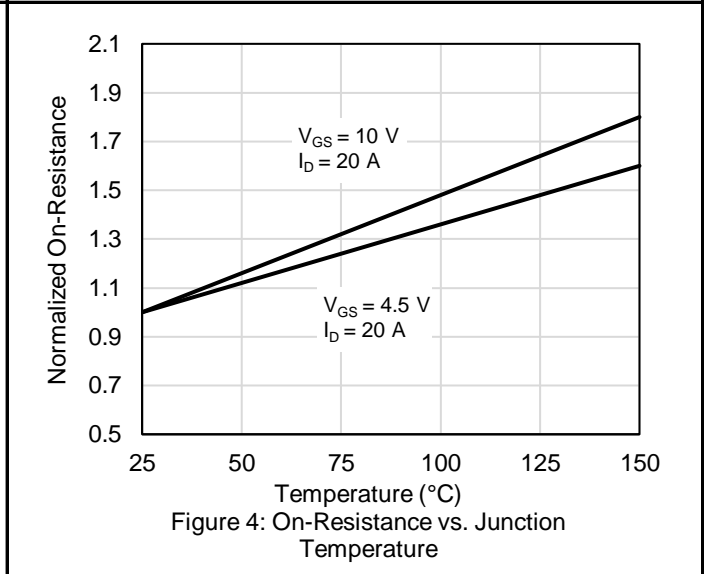
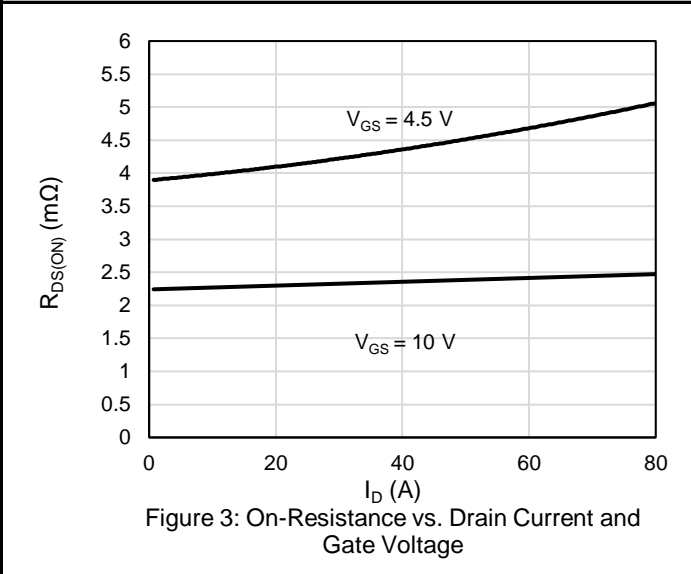
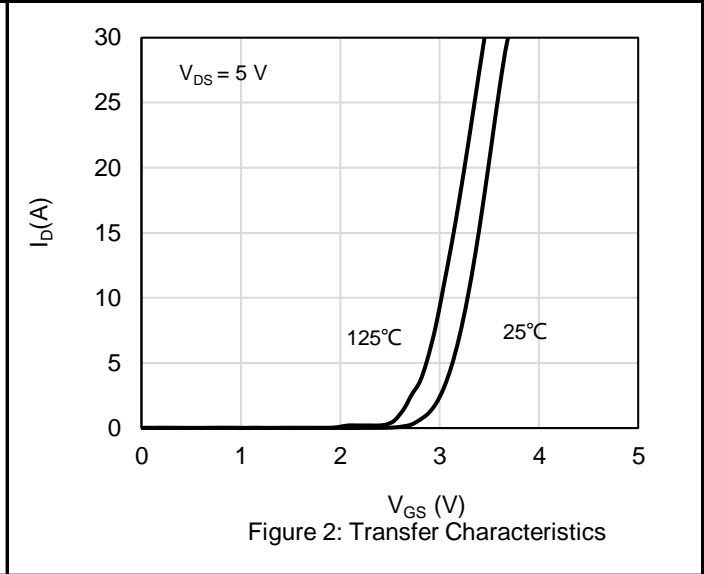
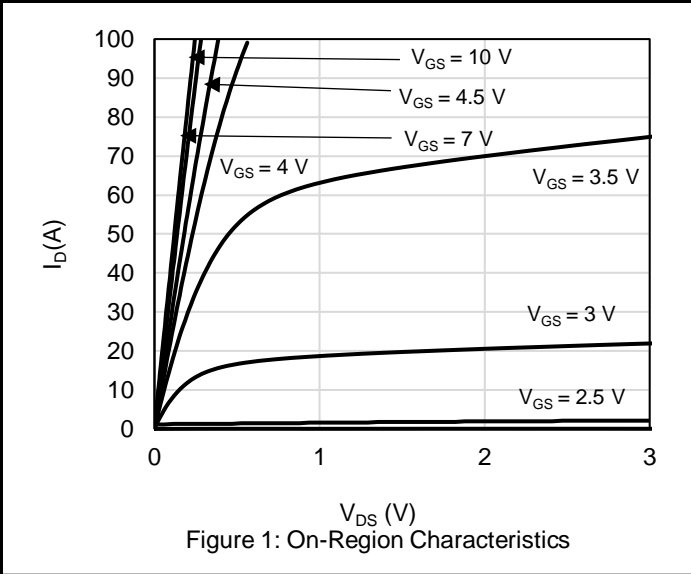
Symbol	Parameter	Value	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Steady-State	2	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Steady State ^(Note 4)	61	$^\circ\text{C}/\text{W}$

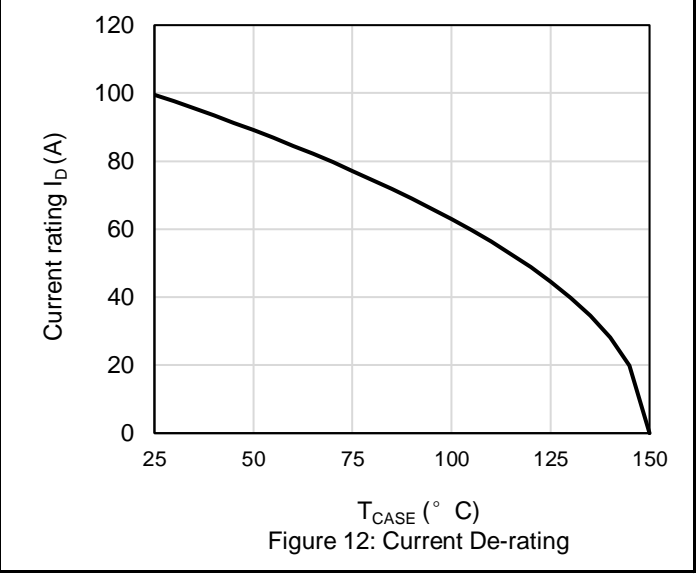
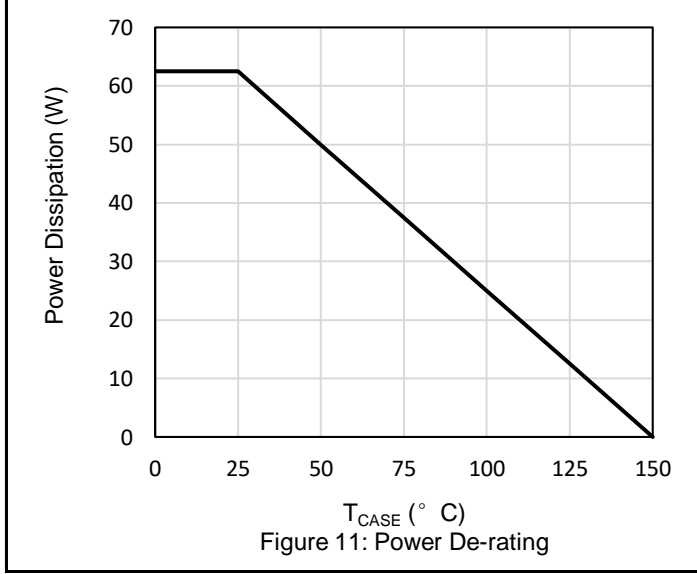
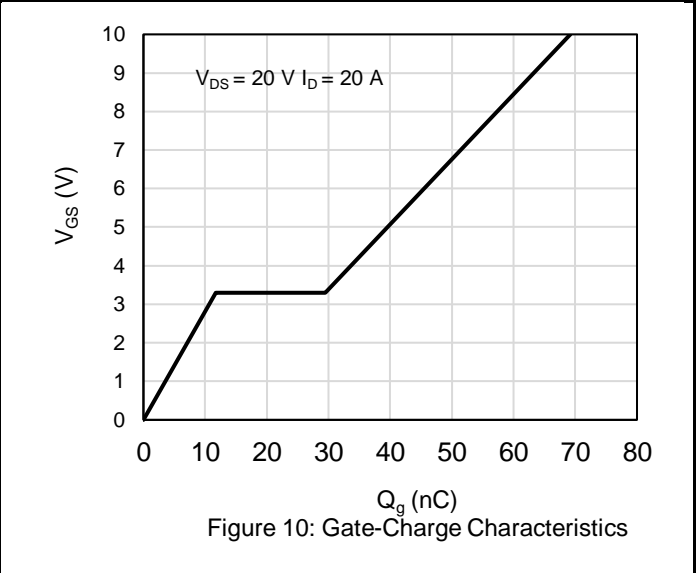
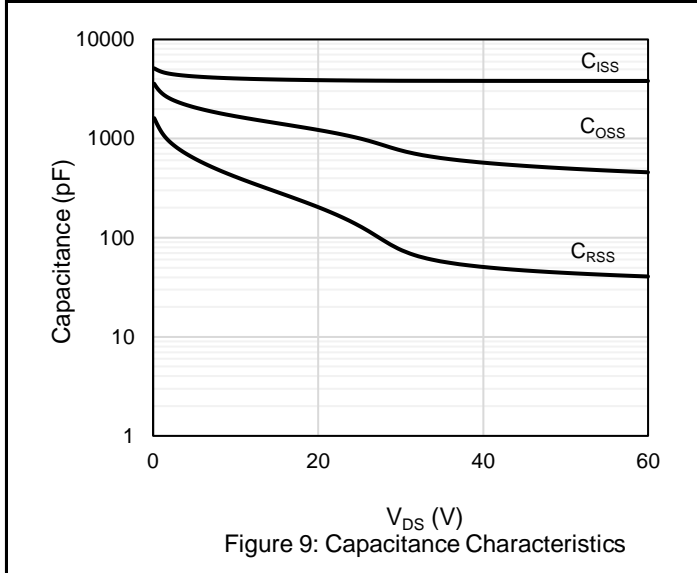
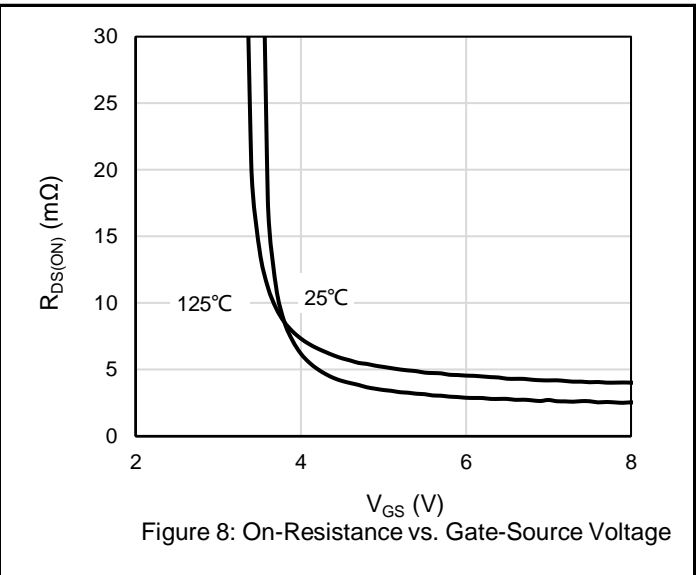
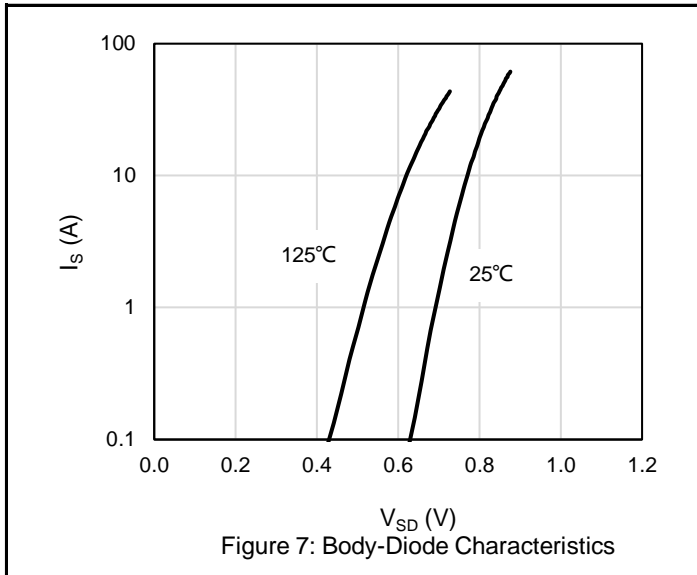
Notes:

1. The max drain current rating is package limited
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. $L = 0.5 \text{ mH}$, $V_{DD} = 30 \text{ V}$, $I_{AS} = 28 \text{ A}$, $R_G = 25 \Omega$, Starting $T_J = 25^\circ\text{C}$
4. Mount on minimum PCB layout

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	60			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V},$			1	μA
I_{GSS}	Gate Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$			± 100	nA
$V_{GS(TH)}$	Gate Threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	2	3	V
$R_{DS(ON)}$	Drain-Source on-state resistance	$V_{GS} = 10\text{ V}, I_D = 20\text{ A}$		2.3	3.5	m Ω
		$V_{GS} = 4.5\text{ V}, I_D = 15\text{ A}$		4.1	5.5	m Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V},$ $F = 1\text{ MHz}$		3828		pF
C_{OSS}	Output Capacitance			773		pF
C_{RSS}	Reverse Transfer Capacitance			78		pF
R_G	Gate Resistance	$F = 1\text{ MHz}$		1.1		Ω
Switching Characteristics						
$T_{D(ON)}$	Turn On Delay Time	$V_{DD} = 30\text{ V}, R_L = 1.5\ \Omega,$ $V_{GS} = 10\text{ V}, R_G = 6\ \Omega$		18		nS
T_R	Rise Time			51.0		nS
$T_{D(OFF)}$	Turn Off Delay Time			61.0		nS
T_F	Fall Time			65.5		nS
Q_G	Total Gate Charge	$V_{DD} = 30\text{ V}, I_D = 20\text{ A},$ $V_{GS} = 10\text{ V}$		69.2		nC
Q_{GS}	Gate-Source Charge			11.7		nC
Q_{GD}	Gate-Drain Charge			17.8		nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Body-Diode Forward Current			100		A
I_{SM}	Maximum Pulsed Body-Diode Forward Current ^(NOTE 1)			400		A
V_{SD}	Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 1\text{ A}$		0.7	1	V
T_{RR}	Reverse recovery time	$V_{DD} = 30\text{ V}, I_D = 20\text{ A},$ $di/dt = 100\text{ A}/\mu\text{S}$		44.5		nS
Q_{RR}	Reverse recovery charge			52.0		nC
I_{RRM}	Peak Reverse Recovery Current			2		A

Electrical Characteristics Diagrams





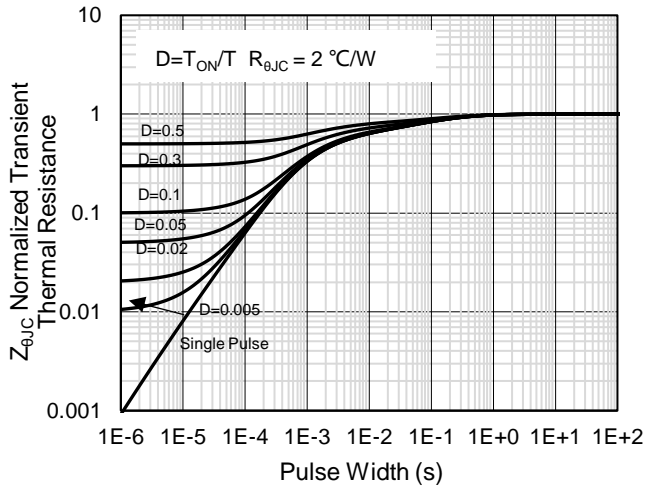


Figure 13: Normalized Maximum Transient Thermal Impedance

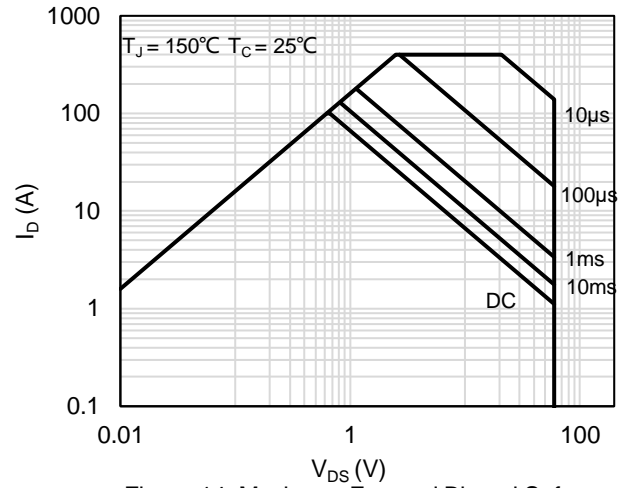
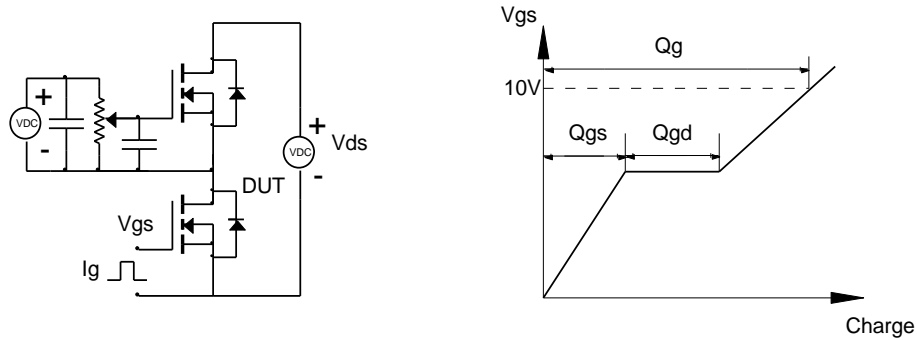


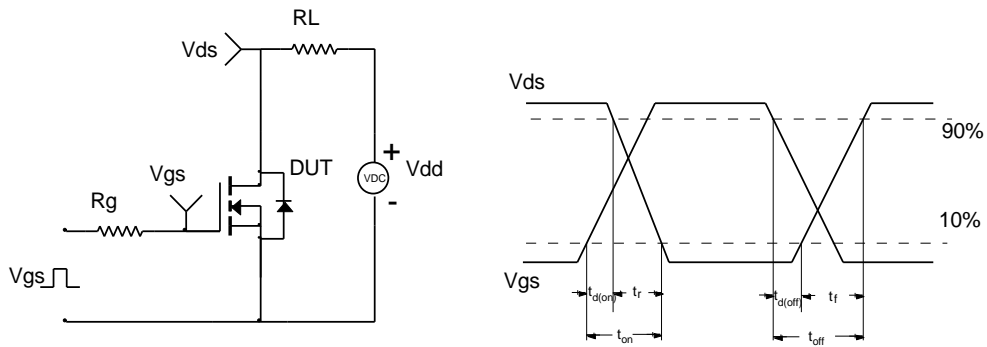
Figure 14: Maximum Forward Biased Safe Operating Area

Test Circuit and Waveform

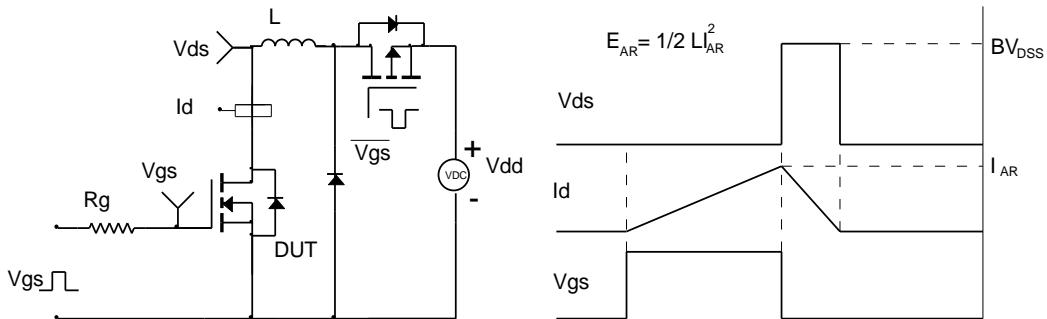
Gate Charge Test Circuit & Waveform



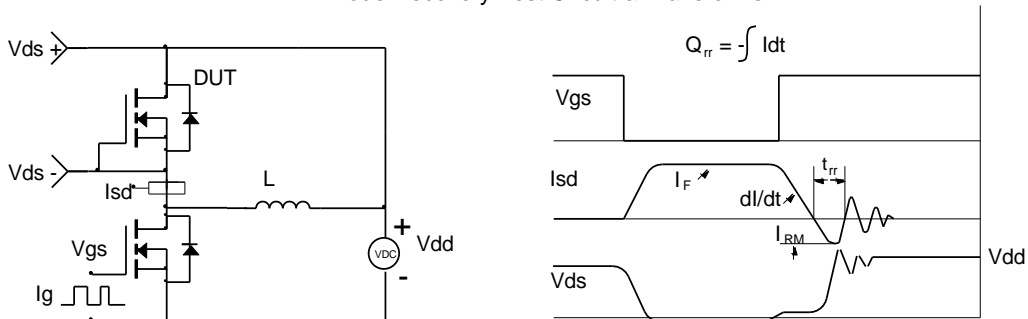
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



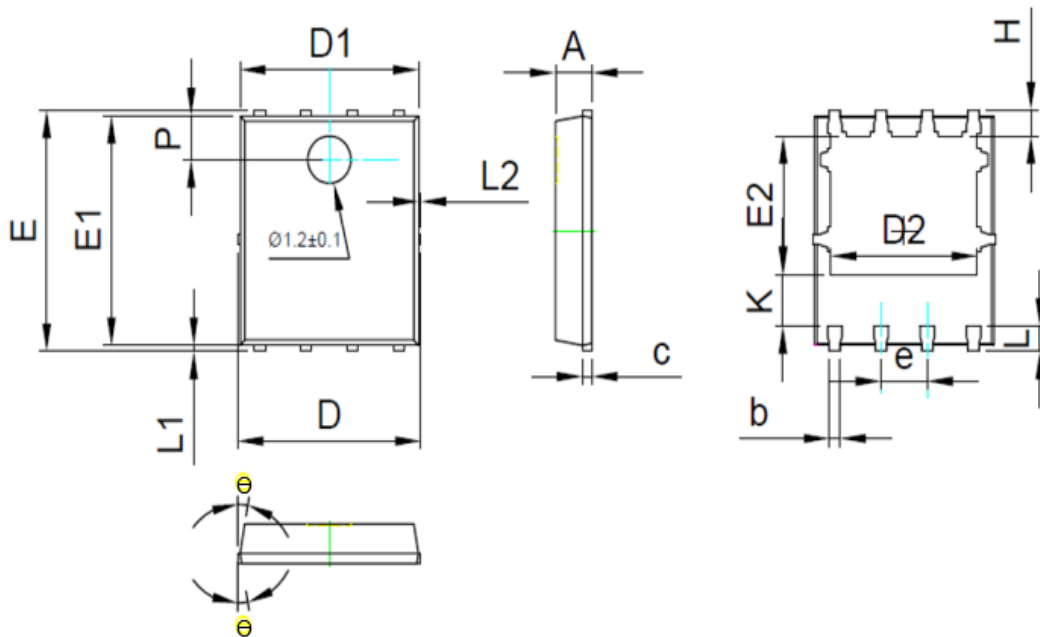
Diode Recovery Test Circuit & Waveforms



Package Outlines

Package Dimensions : PDFN 5*6 PACKAG

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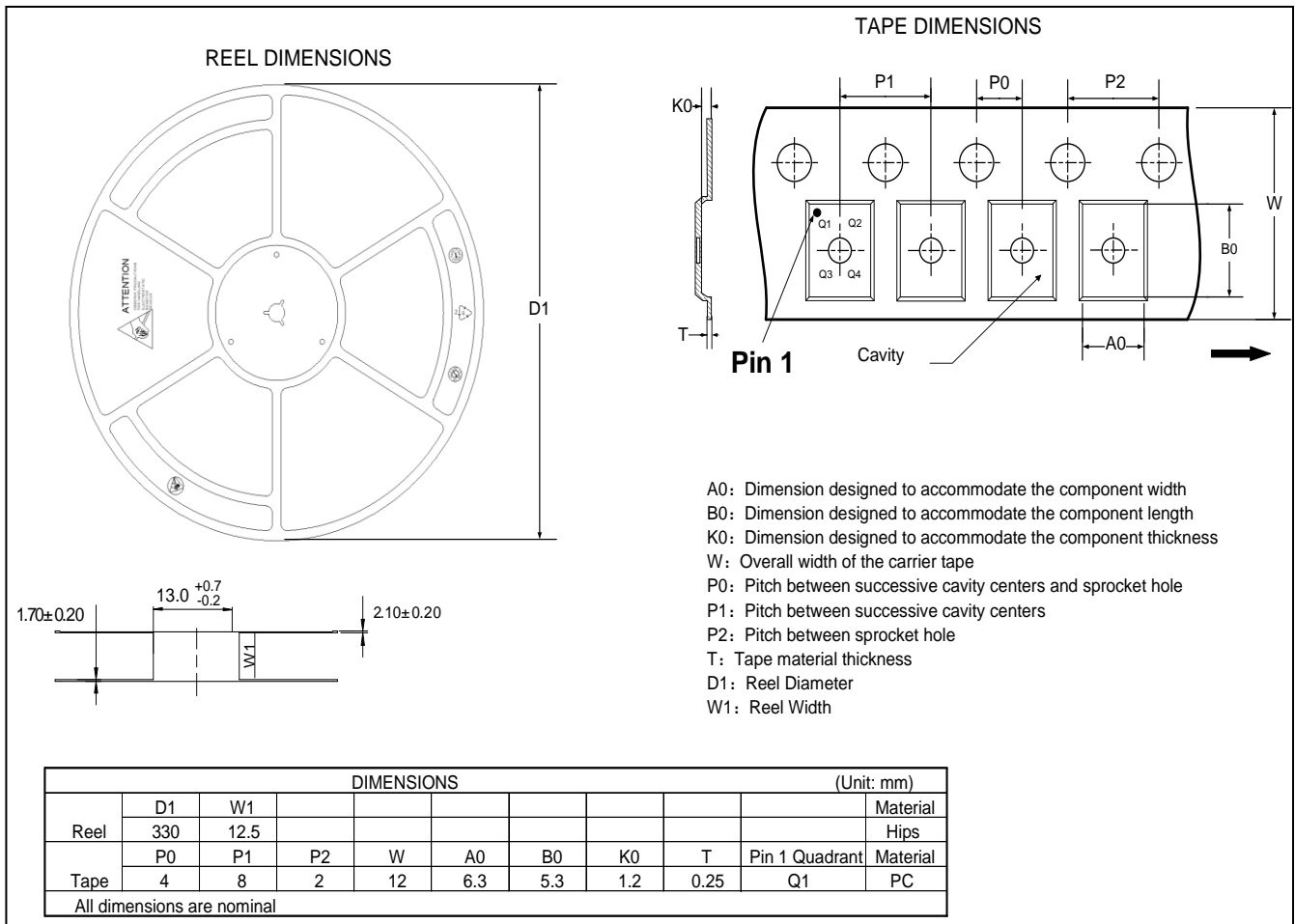
COMMON DIMENSIONS
(UNITS OF MEASURE = MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.90	1.00	1.10
b	0.35	0.40	0.45
c	0.21	0.25	0.34
D	-	-	5.1
D1	4.85	4.90	4.95
D2	3.96	4.01	4.06
e	1.27 BSC		
E	5.95	6.00	6.05
E1	5.70	5.75	5.80
E2	3.425	3.475	3.525
H	0.60	0.65	0.70
K	1.29	-	-
L	0.60	0.65	0.70
L1	0.05	0.15	0.25
L2	-	-	0.12
θ	8°	10°	12°
P	1.05	1.10	1.15

Marking Information



Note:
 G6N035GL = Product Name Code
 XXXXXXXX = Date code
 Contact ALKAIDSEMI sales for detail information



Revision History

Revision	Release Date	Remark
Rev.1.0	2022/7/13	Initial Release

Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

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Due to product or technical improvements, the information described or contained herein may be changed without prior notice.